

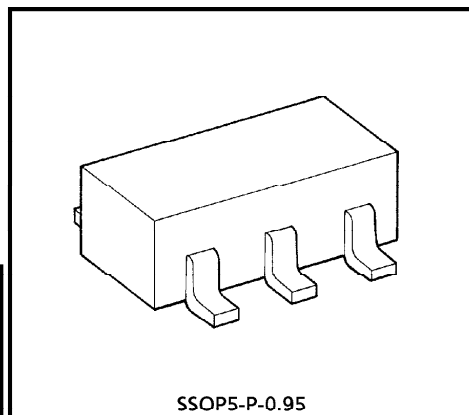
TC4S11F

2 INPUT NAND GATE

The TC4S11F is 2-input positive logic NAND gates. Gate output with inverter buffer improve the input-output characteristics and even if the load capacitance increases, it can be stopped the change of propagation time.

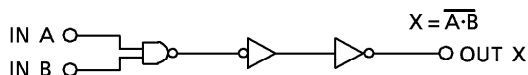
MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
DC Supply Voltage	V _{DD}	V _{SS} - 0.5 ~ V _{SS} + 20	V
Input Voltage	V _{IN}	V _{SS} - 0.5 ~ V _{DD} + 0.5	V
Output Voltage	V _{OUT}	V _{SS} - 0.5 ~ V _{DD} + 0.5	V
DC Input Current	I _{IN}	± 10	mA
Power Dissipation	P _D	200	mW
Operating Temperature Range	T _{opr}	- 40 ~ 85	°C
Storage Temperature Range	T _{stg}	- 65 ~ 150	°C
Lead Temperature (10s)	T _L	260	°C

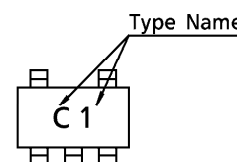


SSOP5-P-0.95
Weight : 0.016g (Typ.)

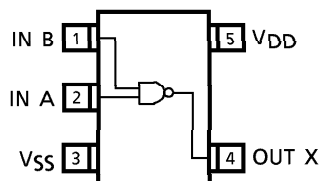
LOGIC DIAGRAM



MARKING



PIN CONFIGURATION (TOP VIEW)



961001EBA2

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RECOMMENDED OPERATING CONDITIONS ($V_{SS} = 0V$)

CHARACTERISTIC	SYMBOL		MIN.	TYP.	MAX.	UNIT
DC Supply Voltage	V_{DD}	—	3	—	18	V
Input Voltage	V_{IN}	—	0	—	V_{DD}	V

STATIC ELECTRICAL CHARACTERISTICS ($V_{SS} = 0V$)

CHARACTERISTIC	SYM-BOL	TEST CONDITION	V_{DD} (V)	-40°C		25°C			85°C		UNIT	
				MIN.	MAX.	MIN.	TYP.	MAX.	MIN.	MAX.		
High-Level Output Voltage	V_{OH}	$ I_{OUT} < 1\mu A$ $V_{IN} = V_{SS}, V_{DD}$	5	4.95	—	4.95	5.00	—	4.95	—	V	
			10	9.95	—	9.95	10.00	—	9.95	—		
			15	14.95	—	14.95	15.00	—	14.95	—		
Low-Level Output Voltage	V_{OL}	$ I_{OUT} < 1\mu A$ $V_{IN} = V_{DD}$	5	—	0.05	—	0.00	0.05	—	0.05	V	
			10	—	0.05	—	0.00	0.05	—	0.05		
			15	—	0.05	—	0.00	0.05	—	0.05		
Output High Current	I_{OH}	$V_{OH} = 4.6V$ $V_{OH} = 2.5V$ $V_{OH} = 9.5V$ $V_{OH} = 13.5V$ $V_{IN} = V_{SS}, V_{DD}$	5	-0.61	—	-0.51	-1.0	—	-0.42	—	mA	
			5	-2.5	—	-2.1	-4.0	—	-1.7	—		
			10	-1.5	—	-1.3	-2.2	—	-1.1	—		
			15	-4.0	—	-3.4	-9.0	—	-2.8	—		
Output Low Current	I_{OL}	$V_{OL} = 0.4V$ $V_{OL} = 0.5V$ $V_{OL} = 1.5V$ $V_{IN} = V_{DD}$	5	0.61	—	0.51	1.2	—	0.42	—	mA	
			10	1.5	—	1.3	3.2	—	1.1	—		
			15	4.0	—	3.4	12.0	—	2.8	—		
Input High Voltage	V_{IH}	$V_{OUT} = 0.5V, 4.5V$ $V_{OUT} = 1.0V, 9.0V$ $V_{OUT} = 1.5V, 13.5V$ $ I_{OUT} < 1\mu A$	5	3.5	—	3.5	2.75	—	3.5	—	V	
			10	7.0	—	7.0	5.5	—	7.0	—		
			15	11.0	—	11.0	8.25	—	11.0	—		
Input Low Voltage	V_{IL}	$V_{OUT} = 4.5V$ $V_{OUT} = 9.0V$ $V_{OUT} = 13.5V$ $ I_{OUT} < 1\mu A$	5	—	1.5	—	2.25	1.5	—	1.5	V	
			10	—	3.0	—	4.5	3.0	—	3.0		
			15	—	4.0	—	6.75	4.0	—	4.0		
Input Current	H Level	I_{IH}	$V_{IH} = 18V$	18	—	0.1	—	10^{-5}	0.1	—	1.0	μA
	L Level	I_{IL}	$V_{IL} = 0V$	18	—	-0.1	—	-10^{-5}	-0.1	—	-1.0	
Quiescent Device Current	I_{DD}	$V_{IN} = V_{SS}, V_{DD}$ *	5	—	0.25	—	0.001	0.25	—	7.5	μA	
			10	—	0.5	—	0.001	0.5	—	15		
			15	—	1.0	—	0.002	1.0	—	30		

* All valid input combinations.

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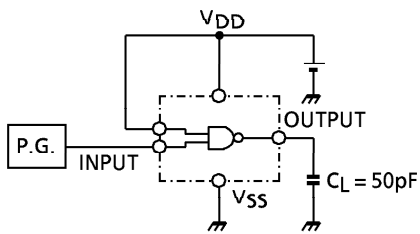
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DYNAMIC ELECTRICAL CHARACTERISTICS (Ta = 25°C, VSS = 0V, CL = 50pF)

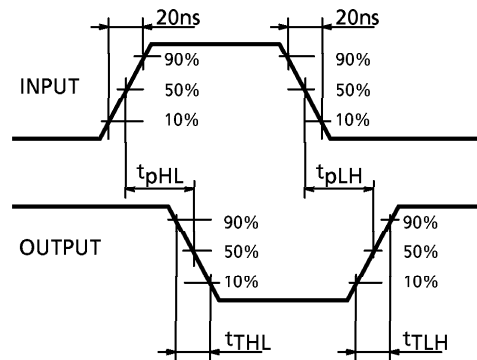
CHARACTERISTIC	SYMBOL	TEST CONDITION	VDD (V)	MIN.	TYP.	MAX.	UNIT
Output Transition Time (Low to High)	t _{TLH}	—	5	—	70	200	ns
			10	—	35	100	
			15	—	30	80	
Output Transition Time (High to Low)	t _{THL}	—	5	—	70	200	ns
			10	—	35	100	
			15	—	30	80	
Propagation Delay Time	t _{pLH}	—	5	—	65	200	ns
			10	—	30	100	
			15	—	25	80	
Propagation Delay Time	t _{pHL}	—	5	—	65	200	ns
			10	—	30	100	
			15	—	25	80	
Input Capacitance	C _{IN}	—	—	5	7.5	pF	

CIRCUIT AND WAVEFORM FOR MEASUREMENT OF DYNAMIC CHARACTERISTICS

TEST CIRCUIT

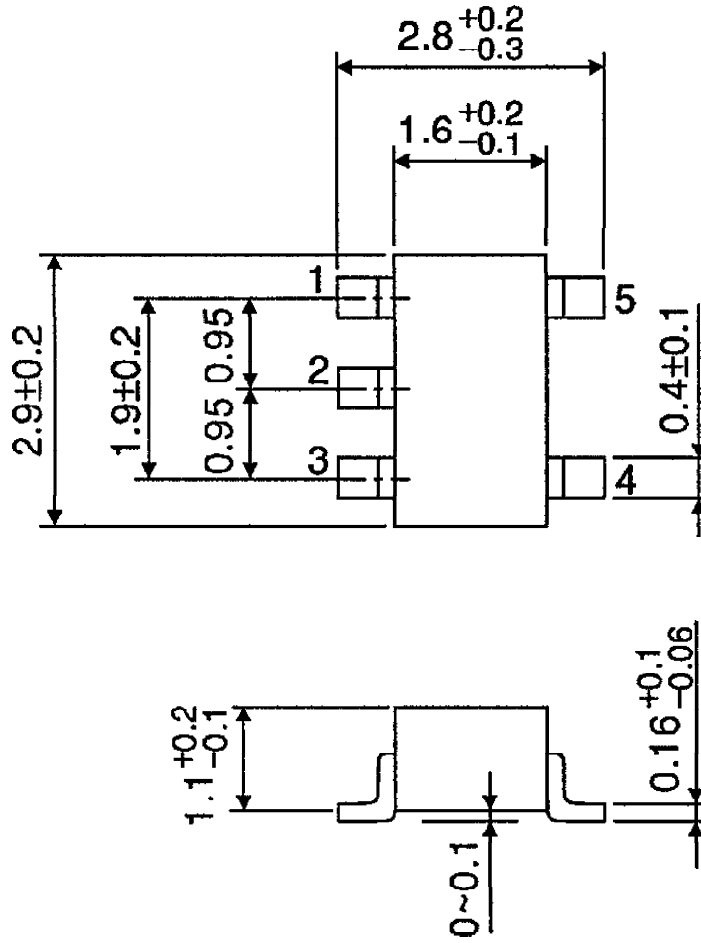


WAVEFORM



OUTLINE DRAWING
SSOP5-P-0.95

Unit : mm



Weight : 0.016g (Typ.)